

# HSM125WK

## Silicon Schottky Barrier Diode for Battery Switch

# HITACHI

Preliminary  
Rev.0  
Oct. 1993

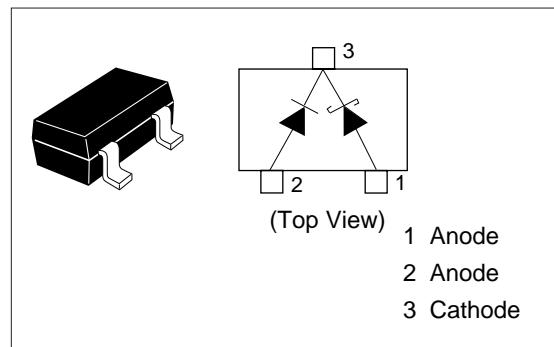
### Features

- The HSM125WK has two different ( $V_F$ -  $I_F$ ) chips, and can change the main battery to the backup battery automatically.
- MPAK package is suitable for high density surface mounting and high speed assembly.

### Ordering Information

Type No.	Laser Mark	Package Code
HSM125WK	S13	MPAK

### Pin Arrangement



### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Value Pin 1-3	Value Pin 2-3	Unit
Peak reverse voltage	$V_{RM}$	20	20	V
Forward current	$I_F$ *	500	100	mA
Junction temperature	$T_j$	125	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	-55 to +125	$^\circ\text{C}$

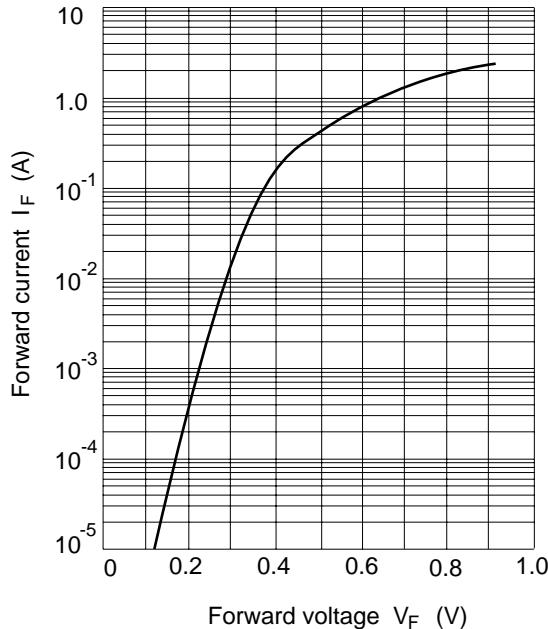
\* Per one device

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

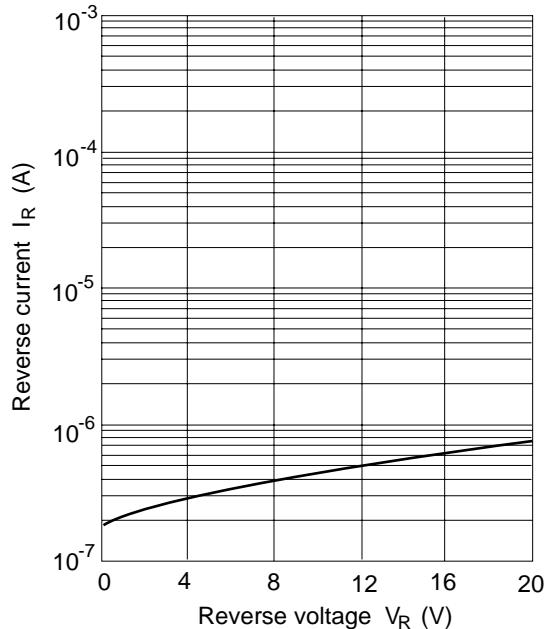
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_{F1}$	Pin 1-3	0.1	—	0.3	$I_F = 1 \text{ mA}$
		Pin 2-3	0.5	—	0.8	
Forward voltage	$V_{F2}$	Pin 1-3	—	—	0.55	$I_F = 500 \text{ mA}$
		Pin 2-3	—	—	1.2	
Reverse current	$I_R$	Pin 1-3	—	—	30	$V_R = 20 \text{ V}$
		Pin 2-3	—	—	0.1	
ESD Capability	—	200	—	—	V	* C=200pF, Both forward and reverse direction 1 pulse

\* Failure Criterion ; Pin 1-3 ( $I_R \geq 60\mu\text{A}$  at  $V_R = 20\text{V}$ ) , Pin 2-3 ( $I_R \geq 0.2\mu\text{A}$  at  $V_R = 20\text{V}$ )

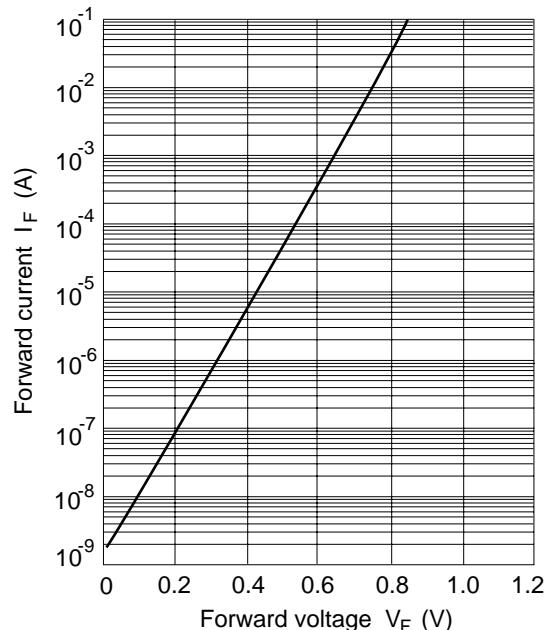
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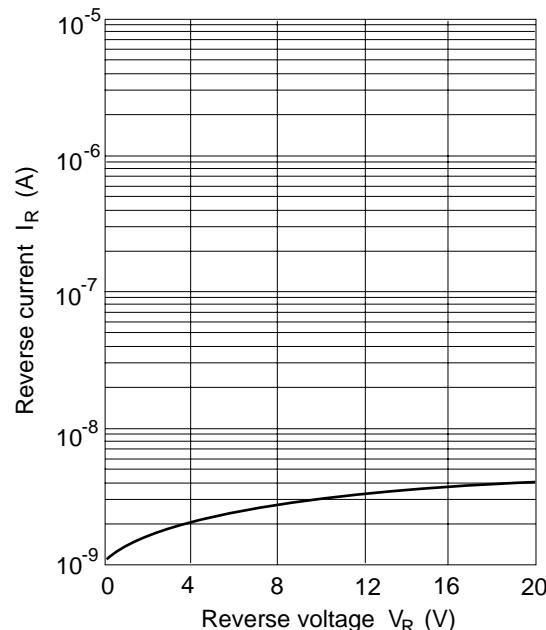
**Fig.1** Forward current Vs.  
Forward voltage  
(Pin1-3)



**Fig.2** Reverse current Vs.  
Reverse voltage  
(Pin1-3)



**Fig.3** Forward current Vs.  
Forward voltage  
(Pin2-3)



**Fig.4** Reverse current Vs.  
Reverse voltage  
(Pin2-3)

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## Package Dimensions

Unit: mm

